

N-channel TrenchMOS standard level FET Rev. 02 — 17 June 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

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Motors, lamps and solenoids

	Quick reference ua	la				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	21.7	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	89	W
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	$\label{eq:GS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 13 \text{ A}; \\ T_{j} = 175 \ ^{\circ}\text{C}; \text{ see } \underline{\text{Figure } 12}; \\ \text{see } \underline{\text{Figure } 13} \end{array}$	-	-	187	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 13 \text{ A};$ T _j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	64	75	mΩ
Avalanche	e ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 14 \text{ A}; V_{sup} \leq 100 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	100	mJ

N-channel TrenchMOS standard level FET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK7275-100A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

N-channel TrenchMOS standard level FET

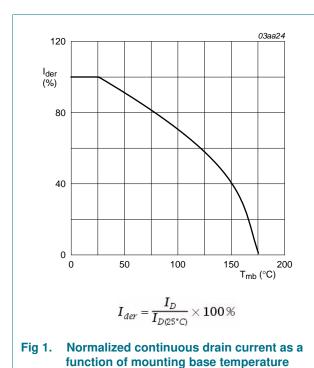
4. Limiting values

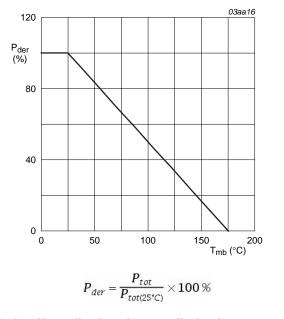
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	100	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>		-	-	21.7	Α
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>		-	-	15.4	А
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see Figure 3	[1]	-	-	87	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	89	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drain	diode						
I _S	source current	T _{mb} = 25 °C		-	-	21.7	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	87	А
Avalanche ru	Iggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 14 \text{ A}; \ V_{sup} \leq 100 \ \text{V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \ \text{V}; \ T_{j(\text{init})} = 25 \ ^\circ\text{C}; \ \text{unclamped} \end{array}$		-	-	100	mJ

[1] Peak drain current is limited by chip, not package.

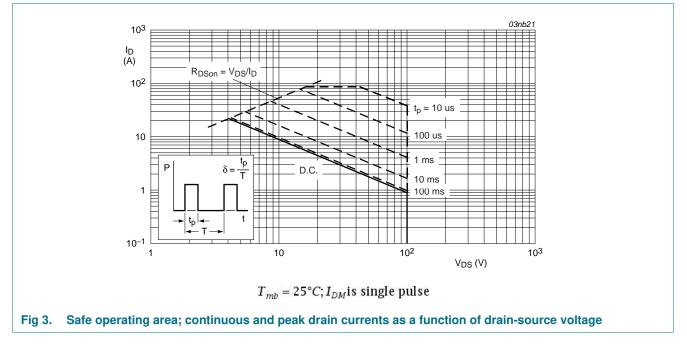






BUK7275-100A

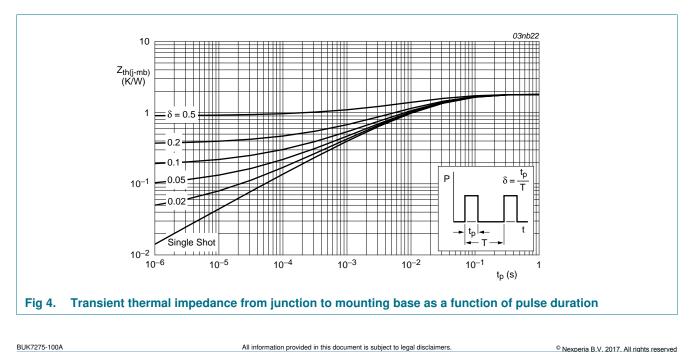
N-channel TrenchMOS standard level FET



Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	71.4	-	K/W



N-channel TrenchMOS standard level FET

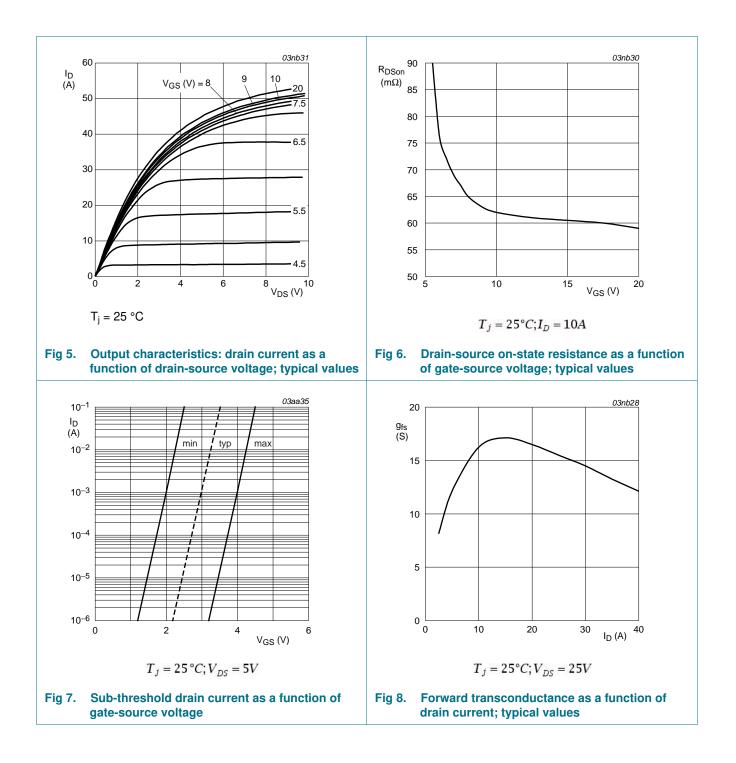
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} d	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u>	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 11</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	1	-	-	V
DSS	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 °C$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 13 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	187	mΩ
		$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 13 \text{ A}; \text{ T}_{j} = 25 \text{ °C};$ see Figure 12; see Figure 13	-	64	75	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	910	1210	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	130	152	pF
C _{rss}	reverse transfer capacitance		-	80	107	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 2.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	8	-	ns
r	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	39	-	ns
d(off)	turn-off delay time		-	26	-	ns
f	fall time		-	24	-	ns
L _D	internal drain inductance	measured from drain lead from package to centre of die	-	2.5	-	nH
-s	internal source inductance	measured from source lead from package to source bond pad	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
•rr	reverse recovery time	$I_{S} = 13 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	64	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	120	-	nC

BUK7275-100A Product data sheet

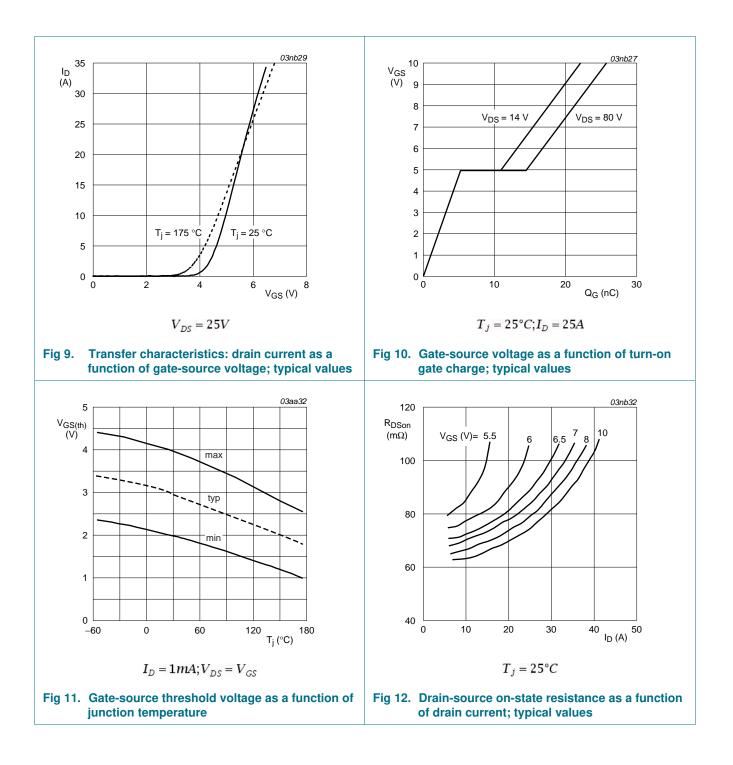
BUK7275-100A

N-channel TrenchMOS standard level FET



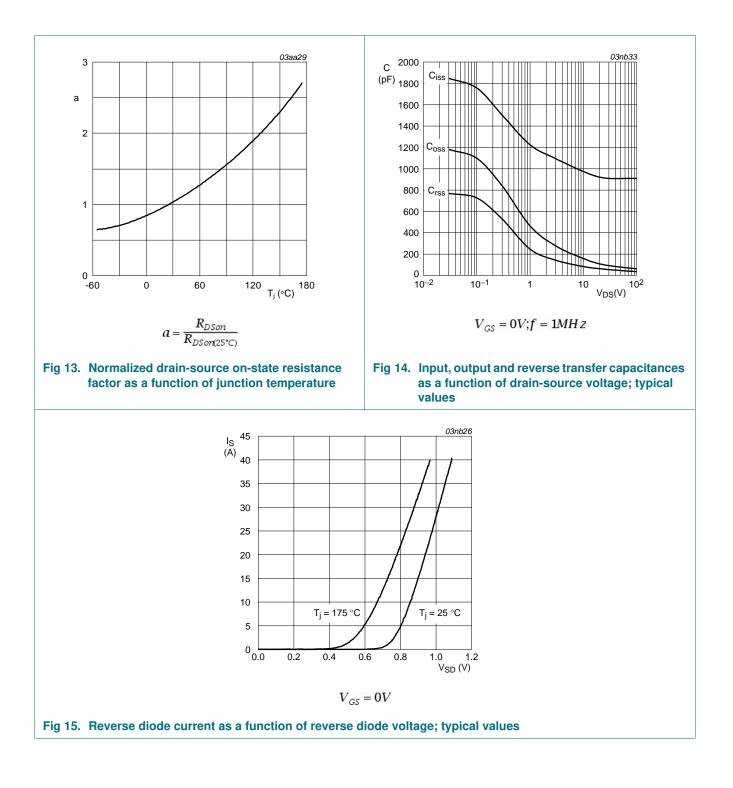
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N-channel TrenchMOS standard level FET



BUK7275-100A

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BUK7275-100A Product data sheet

N-channel TrenchMOS standard level FET

7. Package outline

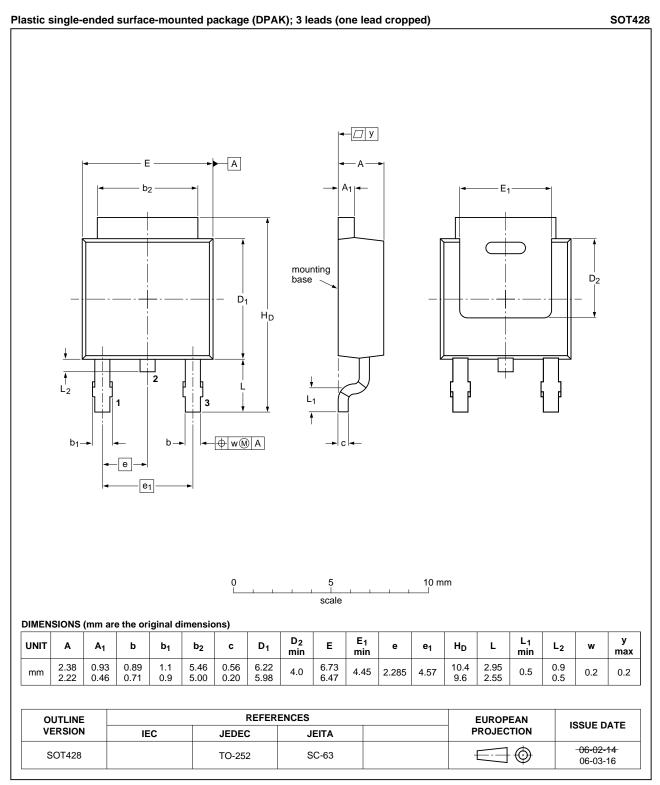


Fig 16. Package outline SOT428 (DPAK)

BUK7275-100A Product data sheet

N-channel TrenchMOS standard level FET

8. Revision history

Table 7.Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7275-100A v.2	20100617	Product data sheet	-	BUK7275-100A v.1
Modifications:	of NXP Se	miconductors.	en redesigned to comply ne new company name w	with the new identity guidelines here appropriate.
BUK7275-100A v.1 (9397 750 07645)	20001025	Product Specification	-	-

N-channel TrenchMOS standard level FET

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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N-channel TrenchMOS standard level FET

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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status11
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12